

Amendments to the Claims:

This listing of claims will replace all prior versions, and listings, of claims in the application:

Listing of Claims:

1. (original) A method of contacting terminals, the method comprising;
 providing a substrate having a substrate surface, the substrate comprising a first terminal having a first terminal surface, and a second terminal having a second terminal surface, wherein a distance between the first terminal surface and the substrate surface is smaller than a distance between the second terminal surface and the substrate surface;
 forming a first insulating layer on the substrate surface and on the first and second terminal surfaces;
 forming a contact via in the first insulating layer for exposing the first terminal surface;
 filling the contact via with a conductive material;
 forming a second insulating layer on the first insulating layer and on the contact via filled with the conductive material;
 forming a etching mask on the second insulating layer, the etching mask specifying an area for a first contact terminal and an area for a second terminal;
 etching a first recess through the second insulating layer for exposing the conductive material filling the contact via, and etching a second recess through the second and first insulating layers for exposing the second terminal surface using the etching mask;
 introducing a conductive material into the first recess and into the second recess for producing the first and second contact terminals.

2. (currently amended) The method as claimed in claim 1, wherein the first terminal is comprises one of a base terminal ~~or and~~ a collector terminal, and the second terminal is comprises an emitter terminal, arranged on a stack, of a bipolar transistor.

3. (currently amended) The method as claimed in claim 1, wherein the first terminal is comprises one of a source ~~or and~~ a drain terminal, and the second terminal is comprises a gate terminal of a field-effect transistor.

4. (currently amended) The method as claimed in claim 1, wherein the one or several first terminals ~~terminal are provided on the substrate, which are~~ is selected from the group of a base terminal of a bipolar transistor, ~~or~~ a collector terminal of a bipolar transistor, ~~or~~ a gate terminal of a field effect transistor, a source terminal of a field effect transistor ~~or and~~ a drain terminal of a field-effect transistor, ~~respectively~~.

5. (currently amended) The method as claimed in claim 1, wherein introducing the conductive material further comprises introducing metal ~~filling into~~ at least one of the first recess, ~~and/or the conductive material filling and~~ the second recess ~~consist of metal~~.

6. (currently amended) The method as claimed in claim 1, wherein the filling step includes conductive material filling the contact via is with tungsten.

7. (currently amended) The method as claimed in claim 1, wherein introducing the conductive material includes introducing copper ~~introduced~~ into the first and second recesses ~~is copper~~.

8. (currently amended) The method as claimed in claim 1, further including the step of forming a wire plane comprising ~~wherein~~ the first contact terminal and the second contact terminal ~~form a wiring plane~~.

9. (original) The method as claimed in claim 1, wherein the step of forming the contact via includes etching the contact via.

10. (currently amended) The method as claimed in claim 1, wherein the etching step includes etching the first recess and the second recess ~~are etched~~ in one pass.

11. (currently amended) The method as claimed in claim 1, wherein introducing the conductive material is introduced further comprises introducing the conductive material into the first and second recesses, ~~so that the first and second contact terminals are produced~~ in one pass.

12. (original) An arrangement for contacting terminals of a substrate comprising a substrate surface, a first terminal having a first terminal surface, and a second terminal having a second terminal surface, the first terminal surface being located at a shorter distance from the substrate surface than the second terminal surface, the arrangement comprising:

 a first insulating layer on the substrate surface, having an insulation-layer surface being located at a longer distance from the substrate surface than the second terminal surface;

 a second insulating layer arranged on the first insulting layer;

 wherein the first insulating layer has a contact via which extends from the insulation-layer surface to the first terminal surface and is filled with a first conductive material, and wherein the insulating layer has a recess penetrating the former, extending up to the first conductive material, and being filled with a second conductive material; and

 wherein a recess extends to the second terminal surface through the first and second insulating layers, and is filled with a third conductive material.

13. (currently amended) The arrangement as claimed in claim 12, wherein the first terminal is one of a base terminal or and a collector terminal, and the second terminal is an emitter terminal, arranged on a stack, of a bipolar transistor.

14. (currently amended) The arrangement as claimed in claim 12, wherein the first terminal is one of a source terminal and a or drain terminal, and the second terminal is a gate terminal of a field-effect transistor.

15. (currently amended) The arrangement as claimed in claim 12, wherein one or several the first terminal is terminals are formed on the substrate, which are and is selected from the group of a base terminal of a bipolar transistor, or a collector terminal of a bipolar transistor, or a gate terminal of a field-effect transistor, a source terminal of a field-effect transistor and or a drain terminal of a field-effect transistor, respectively.

16. (currently amended) The arrangement as claimed in claim 12, wherein at least one of the first conductive material, and/or the second conductive material and/or and the third conductive material consist of comprises metal.

17. (original) The arrangement as claimed in claim 12, wherein the first conductive material is tungsten.

18. (currently amended) The arrangement as claimed in claim 12, wherein at least one of the second and/or and third conductive materials is/are is copper.

19. (original) The arrangement as claimed in claim 12, wherein the second conductive material is conductively connected to the first conductive material and forms a first contact terminal, and wherein the third conductive material is conductively connected to the second terminal and forms a second contact terminal.

20. (original) The arrangement as claimed in claim 12, wherein the first and second contact terminals form a wiring plane.